## **Analog Power**

## P-Channel 40-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

| PRODU               | JCT S                    | UMMA                  | RY                                    |              |             |      |
|---------------------|--------------------------|-----------------------|---------------------------------------|--------------|-------------|------|
| V <sub>DS</sub> (V) |                          | r <sub>DS(on)</sub>   | ID                                    | <b>)</b> (A) |             |      |
| -40                 | 12                       | 2 @ V <sub>G</sub>    | $_{\rm S} = -10 {\rm V}$              | -            | -14         |      |
| -40                 | 18                       | $18 @ V_{GS} = -4.5V$ |                                       |              | -12         |      |
|                     | S □<br>S □<br>S □<br>G □ |                       | 3x3-8PP<br>5 View<br>8<br>7<br>6<br>5 |              | G o         |      |
|                     |                          | ļ                     |                                       |              | P-Channel I | MOSE |

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED) |   |            |       |    |  |  |
|--|---|------------|-------|----|--|--|
| Parame te r  | Symbol                                  | Maximum    | Units |    |  |  |
| Drain-Source Voltage   |   |            | -40   | v  |  |  |
| Gate-Source Voltage  | V <sub>GS</sub>                         | ±20        | v     |    |  |  |
| Continuous Drain Current <sup>a</sup>                                    | $T_A=25^{\circ}C$                       |            | -14   |    |  |  |
| Continuous Drain Current   | $T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$ | ID         | -12   | А  |  |  |
| Pulsed Drain Current <sup>b</sup>  | I <sub>DM</sub>                         | ±50        |       |    |  |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                | Is                                      | -2.1       | А     |    |  |  |
| Deriver Dissingtion <sup>a</sup>   | $T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$ | D.,        | 3.5   | w  |  |  |
| Power Dissipation <sup>a</sup>   | $T_A=70^{\circ}C$                       | гD         | 2.0   | ** |  |  |
| Operating Junction and Storage Temperature Range                         | TJ, Tstg                                | -55 to 150 | °C    |    |  |  |

| THERMAL RESISTANCE RATINGS               |              |                  |       |      |  |  |  |
|--|--------------|------------------|-------|------|--|--|--|
| Parameter                                | Symbol       | Maximm           | Units |      |  |  |  |
| a a a a a a                              | t <= 10 sec  | D                | 35    | °C/W |  |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State | R <sub>0JA</sub> | 81    | °C/W |  |  |  |

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

| SPECIFICATIONS (T <sub>A</sub> = $25^{\circ}$ C UNLESS OTHERWISE NOTED) |                      |   |        |      |      |      |  |  |
|---|----------------------|---|--------|------|------|------|--|--|
| Parameter   | Symbol               | Test Conditions   | Limits |      |      | Unit |  |  |
| i arameter  | Symbol               |   |        | Тур  | Max  | Unit |  |  |
| Static  |                      |   |        |      |      |      |  |  |
| Gate-Threshold Voltage  | $V_{GS(th)}$         | $V_{DS} = V_{GS}, I_D = -250 \text{ uA}$                                  | -1     |      |      | V    |  |  |
| Gate-Body Leakage   | I <sub>GSS</sub>     | $V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$                        |        |      | ±100 | nA   |  |  |
| Zero Gate Voltage Drain Current   |                      | $V_{DS}$ = -32 V, $V_{GS}$ = 0 V  |        |      | -1   | uA   |  |  |
| Zelo Gale Voltage Dialit Current  | I <sub>DSS</sub>     | $V_{DS}$ = -32 V, $V_{GS}$ = 0 V, $T_{J}$ = 55°C                          |        |      | -5   | UA   |  |  |
| On-State Drain Current <sup>A</sup>                                     | I <sub>D(on)</sub>   | $V_{DS}$ = -5 V, $V_{GS}$ = -10 V   | -50    |      |      | Α    |  |  |
| Drain-Source On-Resistance <sup>A</sup>                                 | r <sub>z o</sub> ( ) | $V_{GS}$ = -10 V, $I_{D}$ = -1 A  |        |      | 12   | mΩ   |  |  |
|   | r <sub>DS(on)</sub>  | $V_{GS}$ = -4.5 V, $I_D$ = -1 A   |        |      | 18   |      |  |  |
| Forward Tranconductance <sup>A</sup>                                    | g <sub>fs</sub>      | $V_{DS} = -15 V, I_{D} = -1 A$  |        | 29   |      | S    |  |  |
| Diode Forward Voltage   | V <sub>SD</sub>      | $I_{\rm S}$ = 1 A, $V_{\rm GS}$ = 0 V                                     |        | -0.8 |      | V    |  |  |
| Dynamic <sup>b</sup>  |                      |   |        |      |      |      |  |  |
| Total Gate Charge   | Qg                   | V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -5 V,                          |        | 50   |      | nC   |  |  |
| Gate-Source Charge  | Q <sub>gs</sub>      | v <sub>DS</sub> = -15 v, v <sub>GS</sub> = -5 v,<br>I <sub>D</sub> = -1 A |        | 10   |      |      |  |  |
| Gate-Drain Charge   | Q <sub>gd</sub>      | $I_D = -I A$  |        | 10   |      |      |  |  |
| Turn-On Delay Time  | t <sub>d(on)</sub>   |   |        | 9    |      |      |  |  |
| Rise Time   | tr                   | $V_{DD}$ = -15 V, $R_L$ = 6 $\Omega$ ,                                    |        | 10   |      | nS   |  |  |
| Turn-Off Delay Time   | t <sub>d(off)</sub>  | $I_{D} = -1 A, V_{GEN} = -10 V$   |        | 100  |      |      |  |  |
| Fall-Time   | t <sub>f</sub>       |   |        | 40   |      | 1    |  |  |

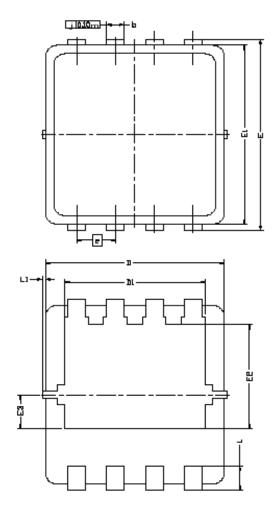
Notes

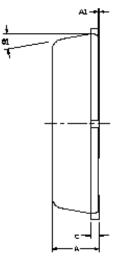
a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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## Package Information





| TIM        | MILLIMETERS        |                    |       | INCHES    |           |        |  |  |
|------------|--------------------|--------------------|-------|-----------|-----------|--------|--|--|
| DIM.       | MIN                | NDM                | MAX   | MIN       | NDM       | MAX    |  |  |
| A          | 0,700              | 0,80               | 0.900 | 0.0276    | 0.0315    | 0,0354 |  |  |
| A1         | 0.00               |                    | 0.05  | 0.000     |           | 0.002  |  |  |
| b          | 0.24               | 0.30               | 0.35  | 0.009     | 0.012     | 0.014  |  |  |
| C          | 0,10               | 0.152              | 0,25  | 0,004     | 0,006     | 0,010  |  |  |
| ם          | 63                 | 28 00.8S           | C     | 0.118 BSC |           |        |  |  |
| D1         | tu<br>tu           | .35 BS             | С     | 0.093 BSC |           |        |  |  |
| Ε          | 3                  | 1,20 BS            | С     | 0,        | 126 BSC   |        |  |  |
| E1         | 3.00 BSC 0.118 BSC |                    |       |           |           | :C     |  |  |
| E5         | 1                  | 1.75 BSC 0.069 BSC |       |           |           | C      |  |  |
| E3         | 0.575 BSC          |                    |       | 0.023 BSC |           |        |  |  |
| 6          | Ó                  | 0.65 BSC           |       |           | 0.026 BSC |        |  |  |
| L          | 0,30               | 0,40               | 0,50  | 0,0118    | 0.0157    | 0.0197 |  |  |
| L1         |                    |                    | 0.100 | D         |           | 0.004  |  |  |
| <b>0</b> 1 | Û°                 | 10*                | 12*   | Ū*        | 10°       | 12°    |  |  |